

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
13 January 2005 (13.01.2005)

PCT

(10) International Publication Number
WO 2005/004201 A3

(51) International Patent Classification⁷: **H01L 21/8222**,
21/331, 27/082

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(21) International Application Number:
PCT/US2004/019906

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(22) International Filing Date: 22 June 2004 (22.06.2004)

(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/604,045 24 June 2003 (24.06.2003) US

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,

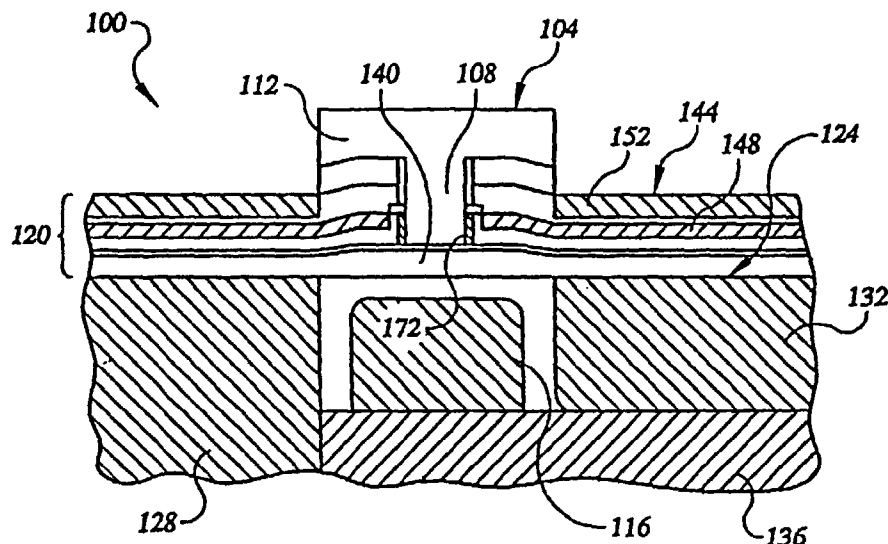
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(54) Title: BIPOLAR TRANSISTOR AND METHOD OF MAKING SAME



(57) Abstract: A high f_T and f_{max} bipolar transistor (100) includes an emitter (104), a base (120), and a collector (116). The emitter has a lower portion (108) and an upper portion (112) that extends beyond the lower portion. The base includes an intrinsic base (140) and an extrinsic base (144). The intrinsic base is located between the lower portion of the emitter and the collector. The extrinsic base extends from the lower portion of the emitter beyond the upper portion of the emitter and includes a continuous conductor (148) that extends from underneath the upper portion of the emitter and out from underneath the upper portion of the emitter. The continuous conductor provides a low electrical resistance path from a base contact (not shown) to the intrinsic base. The transistor may include a second conductor (152) that does not extend underneath the upper portion of the emitter, but which further reduces the electrical resistance through the extrinsic base.

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SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Declarations under Rule 4.17:

- *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE,*

- of inventorship (Rule 4.17(iv)) for US only*

Published:

- *with international search report*

(88) Date of publication of the international search report:
12 May 2005

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.